

2SB0621 (2SB621), 2SB0621A (2SB621A)

Silicon PNP epitaxial planar type

For low-frequency driver amplification

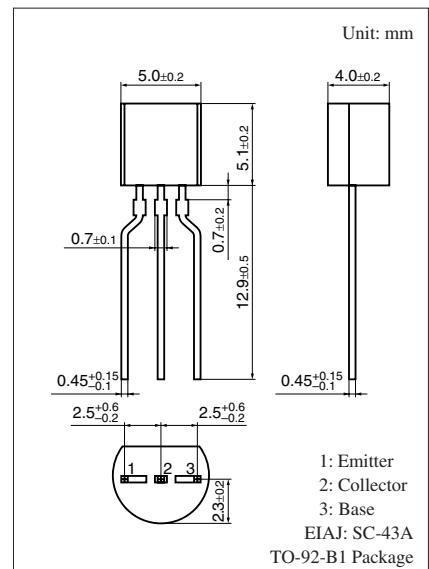
Complementary to 2SD0592 (2SD592), 2SD0592A (2SD592A)

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- High transition frequency f_T

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	2SB0621	V_{CBO}	-30	V
	2SB0621A		-60	
Collector-emitter voltage (Base open)	2SB0621	V_{CEO}	-25	V
	2SB0621A		-50	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_C	-1	A	
Peak collector current	I_{CP}	-1.5	A	
Collector power dissipation	P_C	750	mW	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

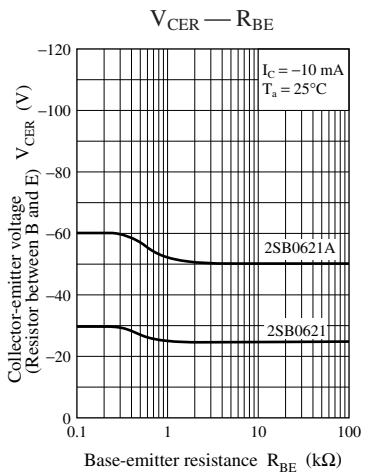
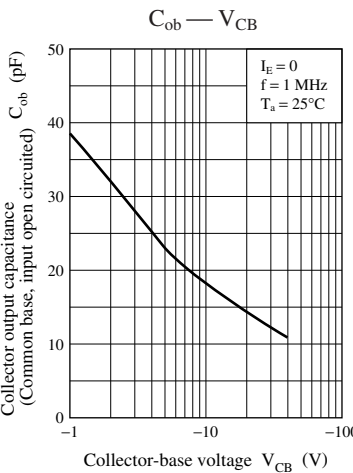
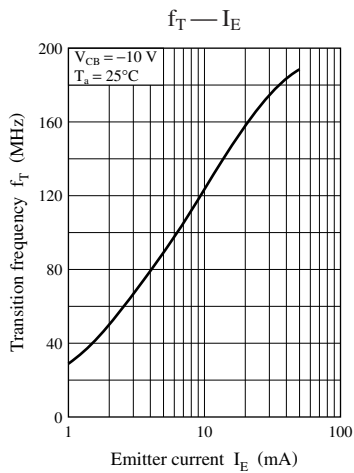
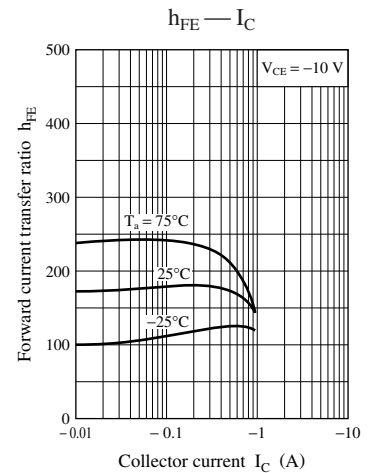
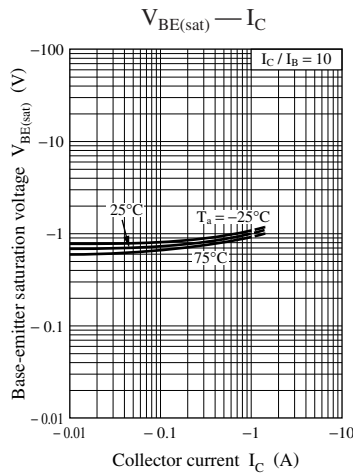
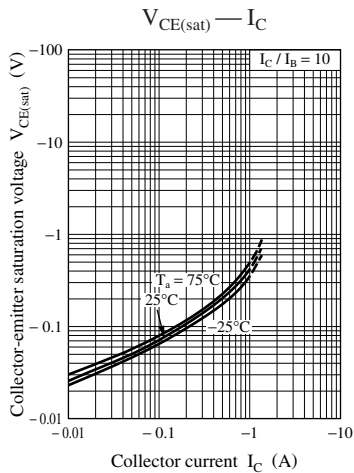
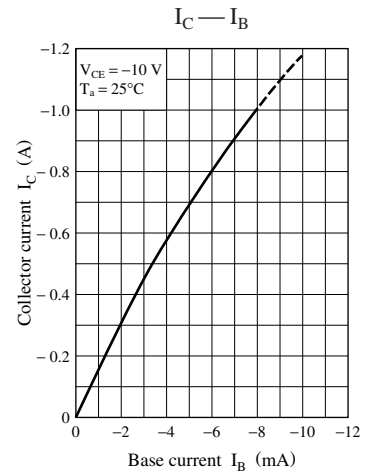
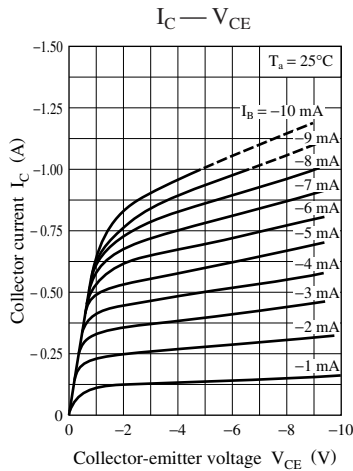
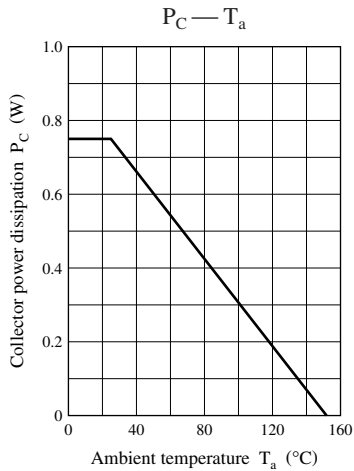
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	2SB0621	V_{CBO}	$I_C = -10 \mu\text{A}$, $I_E = 0$	-30		V
	2SB0621A			-60		
Collector-emitter voltage (Base open)	2SB0621	V_{CEO}	$I_C = -2 \text{ mA}$, $I_B = 0$	-25		V
	2SB0621A			-50		
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}$, $I_C = 0$	-5		V	
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}$, $I_E = 0$			-0.1	μA
Forward current transfer ratio	h_{FE1} *	$V_{CE} = -10 \text{ V}$, $I_C = -500 \text{ mA}$	85		340	—
	h_{FE2}	$V_{CE} = -5 \text{ V}$, $I_C = -1 \text{ A}$	50			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$		-0.2	-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}$, $I_E = 50 \text{ mA}$, $f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		20	30	pF

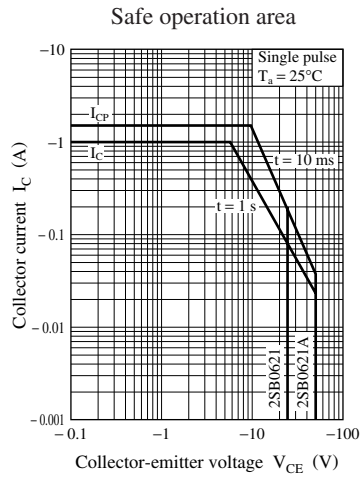
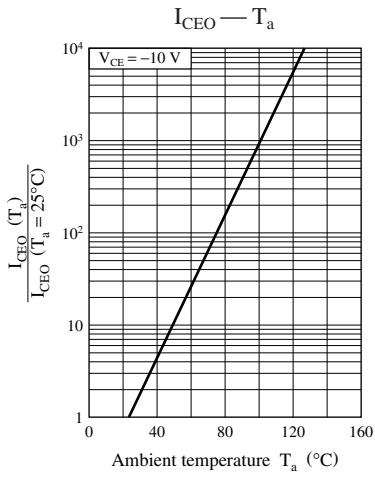
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	R	S
h_{FE1}	85 to 170	120 to 240	170 to 340

Note) The part numbers in the parenthesis show conventional part number.





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